

L Number	Hits	Search Text	DB	Time stamp
1	77206	semic ndu t r adj waf r	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:13
2	30	(semiconductor adj wafer) and barcode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:18
3	3401	(semiconductor adj wafer) and (bar code)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 11:18
4	362	(semiconductor adj wafer) and (bar adj code)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:45
5	123	((semiconductor adj wafer) and (bar adj code)) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:45
6	0	((semiconductor adj wafer) and barcode) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:45
7	0	((semiconductor adj wafer) and barcode) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:45
8	1	((semiconductor adj wafer) and (bar adj code)) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 12:46
9	0	((semiconductor adj wafer) and (bar adj code)) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:34
10	2	6268641.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:00

11	2	6312876.pn.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:00
12	102	430/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:00
13	396	257/620.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 16:00

L Number	Hits	Search Text	DB	Tim stamp
-	1006	235/494.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:55
-	0	235/494.ccls. and chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	0	jp-223380-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	9	"223380"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:57
-	0	jp-223380-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	0	jp-5923512-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	2	jp-2000223380-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	0	jp-2175154-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	1	jp-3116919-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	15423	chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02

-	818	chiba.in. and semiconductor	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	58	(chiba.in. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:05
-	153	(chiba.in. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	83	235/494.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:10
-	8	(235/494.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	34	(235/494.ccls. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:15
-	2	6305677.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:16
-	174	269/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:18
-	81423	semiconductor adj2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4744	(semiconductor adj2 wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19

-	4500	((semiconduc t r adj2 waf r) and mark) and (semiconduc t r adj wafer)	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:20
-	61	((semiconduc t r adj2 waf r) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:26
-	22	semiconductor adj mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1602	355/53.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1154	355/53.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1052	(355/53.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	415	((355/53.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:30
-	8	((355/53.ccls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	5	((355/53.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:34

	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)	USPAT; US-PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
	10	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and notch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
	300	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:38
	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce near erased near marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce same erased same marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
	121	((355/53.ccls. and semiconductor) and wafer) and mark) and identical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:40
	9	((355/53.ccls. and semiconductor) and wafer) and mark) and identical) and reproduce\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
	172	((355/53.ccls. and semiconductor) and wafer) and mark) and prevent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
	3	((355/53.ccls. and semiconductor) and wafer) and mark) and prevent) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53

-	354	355/43. ls.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	84	355/43. cls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	71	(355/43.cls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	1	((355/43.cls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:54
-	45	((355/43.cls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	25968	355/\$.cls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	2116	355/\$.cls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	1469	(355/\$.cls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	497	((355/\$.cls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	8	((355/\$.cls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59

-	13	((355/\$.cls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
-	1	((((355/\$.cls. and semiconductor) and wafer) and mark) and erase) and (((355/\$.cls. and semiconductor) and wafer) and mark) and reproduce)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02